



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-4.2 A

Features

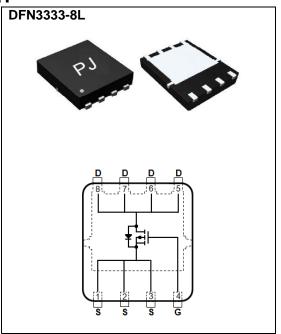
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-6A<68m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_{D}@-3A<85m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _A =25°C	l _D	-4.2	А	
	T _A =70°C		-3.4		
Pulsed Drain Current ^(Note 1)		I _{DM}	-16.8		
Power Dissipation	T _A =25°C		2.1	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	۰C	
Typical Thermal Resistance		$R_{ heta JA}$	59.5	°C/W	

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.53	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-6A	-	55	68	mΩ
		V _{GS} =-4.5V,I _D =-3A	-	71	85	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Qg	V _{DS} =-30V, I _D =-6A,	-	17	-	nC
Gate-Source Charge	Qgs		-	2.8	-	
Gate-Drain Charge	Q_{gd}	VGS=-10 V (1888 8)	-	3.6	-	
Input Capacitance	Ciss	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	879	-	pF
Output Capacitance	Coss	V _{DS} =-30V, V _{GS} =0V, f=1.0MHZ	-	70	-	
Reverse Transfer Capacitance	Crss	I=1.0IVINZ	-	47	-	
Turn-On Delay Time	td _(on)		-	8.4	-	
Turn-On Rise Time	tr	V _{DD} =-30V, I _D =-1A,	-	30	-	ns
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_{G} =6Ω	-	52	-	
Turn-Off Fall Time	t _f	(10.000)	-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	l.		-	-	-4.2	А
Diode Forward Current	I _S					
Diode Forward Voltage	V _{SD}	I _S =-1A,V _{GS} =0V	-	-0.73	-1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

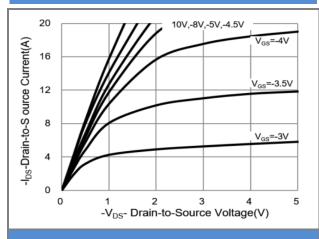


Fig.1 On-Region Characteristics

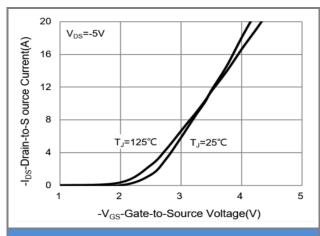


Fig.2 Transfer Characteristics

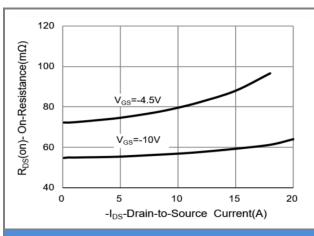


Fig.3 On-Resistance vs. Drain Current

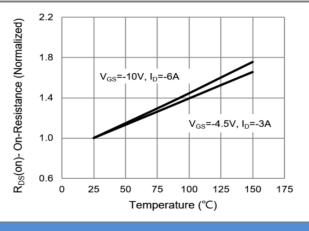


Fig.4 On-Resistance vs. Junction temperature

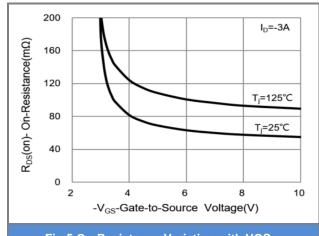


Fig.5 On-Resistance Variation with VGS.

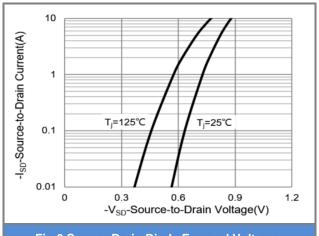


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

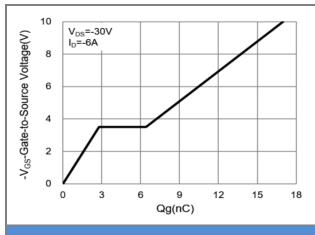


Fig.7 Gate-Charge Characteristics

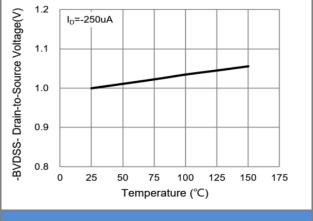


Fig.8 Breakdown Voltage Variation vs. Temperature.

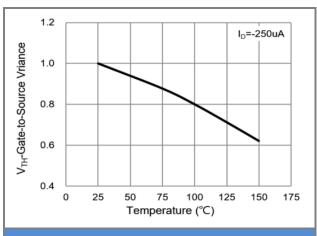


Fig.9 Threshold Voltage Variation with Temperature

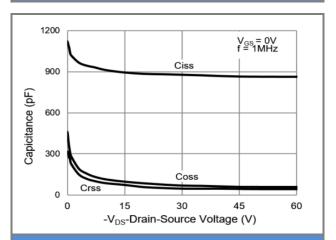


Fig.10 Capacitance vs. Drain-Source Voltage

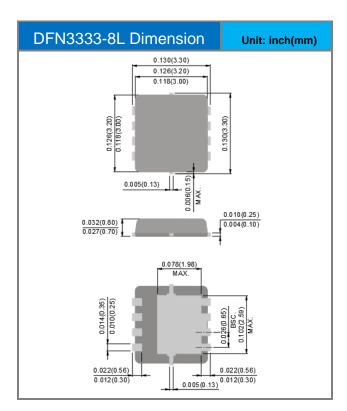


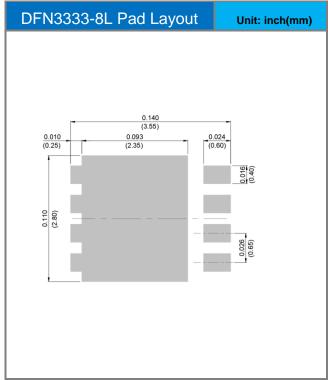


PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4463AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4463	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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